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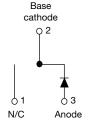
Hyperfast Rectifier, 8 A FRED Pt®

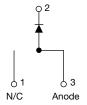




TO-263AB (D²PAK)

TO-262AA





VS-8ETH06SPbF

VS-8ETH06-1PbF

PRODUCT SUMMARY	
Package	TO-263AB (D ² PAK), TO-262AA
I _{F(AV)}	8 A
V_{R}	600 V
V _F at I _F	1.3 V
t _{rr} typ.	18 ns
T _J max.	175 °C
Diode variation	Single die

FEATURES

- Hyperfast recovery time
- Low forward voltage drop
- Low leakage current
- 175 °C operating junction temperature
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C



- AEC-Q101 qualified
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of SMPS, inverters or as freewheeling diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS		
Peak repetitive reverse voltage	V_{RRM}		600	V		
Average rectified forward current	I _{F(AV)}	T _C = 144 °C	8			
Non-repetitive peak surge current	I _{FSM}	T _J = 25 °C	90	Α		
Peak repetitive forward current	I _{FM}		16			
Operating junction and storage temperatures	T_J , T_{Stg}		-65 to +175	°C		

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Breakdown voltage, blocking voltage	V _{BR} , V _R	Ι _R = 100 μΑ	600	-	-			
Forward voltage	V _F	I _F = 8 A	-	2.0	2.4	V		
Forward voltage		I _F = 8 A, T _J = 150 °C	-	1.3	1.8			
Develope legicome eviment		$V_R = V_R$ rated	-	0.3	50			
Reverse leakage current I _R	IR	T _J = 150 °C, V _R = V _R rated	-	55	500	μΑ		
Junction capacitance	C _T	V _R = 600 V	-	17	-	pF		
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8.0	=	nH		



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DYNAMIC RECOVERY CHARACTERISTICS (T _C = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS
		I _F = 1 A, dI _F /dt = 1	00 A/μs, V _R = 30 V	-	18	22	ns
Payersa rasayany tima		$I_F = 8 \text{ A}, dI_F/dt = 1$	00 A/μs, V _R = 30 V	-	20	25	
Reverse recovery time	t _{rr}	T _J = 25 °C		-	25	-	
		T _J = 125 °C	$I_F = 8 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_B = 390 \text{ V}$	-	40	-	
Deals recovery average	I _{RRM}	T _J = 25 °C		-	2.4	-	А
Peak recovery current		T _J = 125 °C		-	4.8	-	
Develop receiver above	Q _{rr}	T _J = 25 °C	1	-	25	-	nC
Reverse recovery charge		T _J = 125 °C		-	120	-	nc
Reverse recovery time	t _{rr}		I _F = 8 A	-	33	-	ns
Peak recovery current	I _{RRM}	T _J = 125 °C	$dI_F/dt = 600 A/\mu s$	-	12	-	Α
Reverse recovery charge	Q _{rr}	1	V _R = 390 V	-	220	-	nC

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C
Thermal resistance, junction to case per leg	R _{thJC}		-	1.4	2	
Thermal resistance, junction to ambient per leg	R _{thJA}	Typical socket mount	-	-	70	°C/W
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.5	-	
Maight			-	2.0	-	g
Weight			-	0.07	-	oz.
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)
Madian da inc		Case style TO-263AB (D ² PAK)	8ETH06S			
Marking device		Case style TO-262AA	8ETH06-1			



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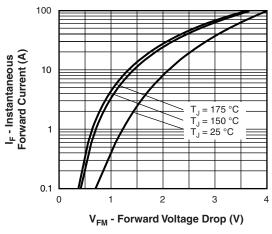


Fig. 1 - Maximum Forward Voltage Drop Characteristics

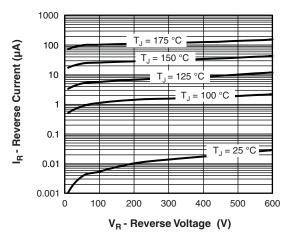


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

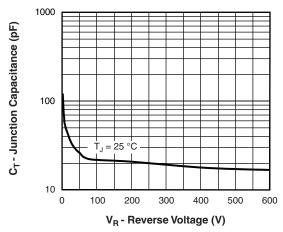


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

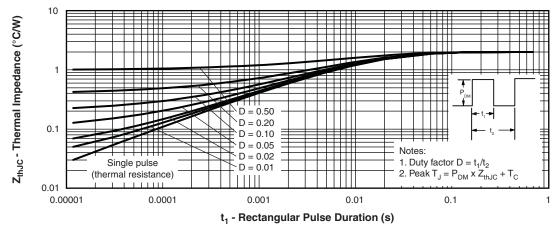


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics



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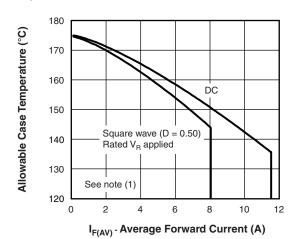


Fig. 5 - Maximum Allowable Case Temperature vs.
Average Forward Current

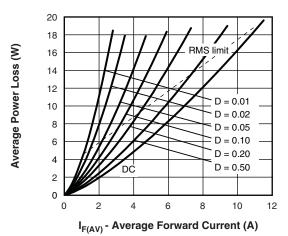


Fig. 6 - Forward Power Loss Characteristics

Note

 $\begin{array}{ll} \text{(1)} & \text{Formula used: } T_C = T_J - (Pd + Pd_{REV}) \times R_{th,JC}; \\ Pd = \text{Forward power loss} = I_{F(AV)} \times V_{FM} \text{ at } (I_{F(AV)}/D) \text{ (see fig. 6)}; \\ Pd_{REV} = \text{Inverse power loss} = V_{R1} \times I_R \text{ (1 - D); } I_R \text{ at } V_{R1} = \text{Rated } V_R \\ \end{array}$

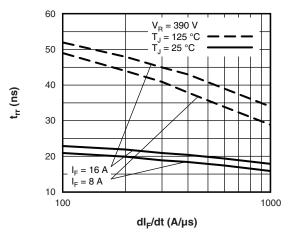


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

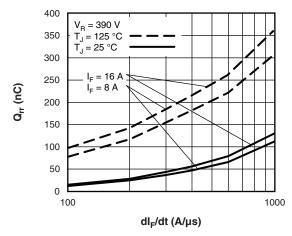


Fig. 8 - Typical Stored Charge vs. dl_F/dt

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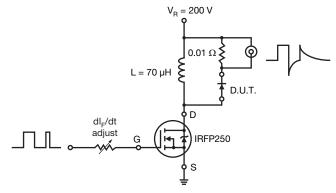
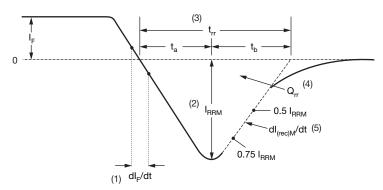


Fig. 9 - Reverse Recovery Parameter Test Circuit



- dl_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm I_{F}$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) Q_{rr} area under curve defined by t_{rr} and I_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $dl_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

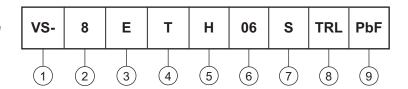
Fig. 10 - Reverse Recovery Waveform and Definitions

VS-8ETH06SPbF, VS-8ETH06-1PbF

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ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - Current rating (8 A)

3 - E = single diode

4 - T = TO-220, D^2PAK

5 - H = hyperfast rectifier

6 - Voltage rating (06 = 600 V)

7 - • S = D²PAK

• -1 = TO-262

None = tube (50 pieces)

• TRL = tape and reel (left oriented, for D²PAK package)

• TRR = tape and reel (right oriented, for D²PAK package)

9 - PbF = lead (Pb)-free

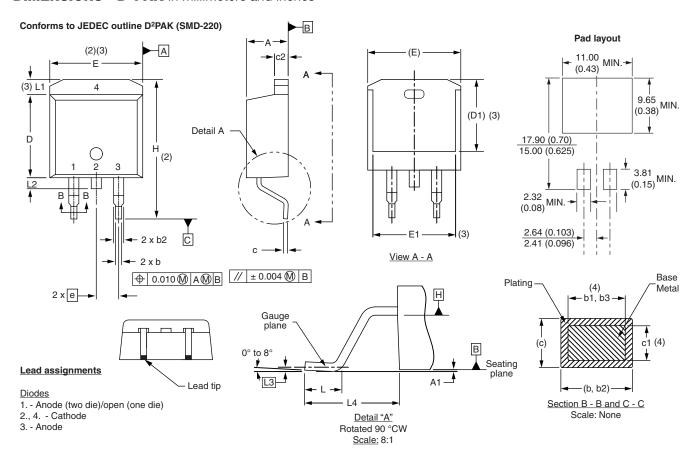
LINKS TO RELATED DOCUMENTS						
Dimensions <u>www.vishay.com/doc?95014</u>						
Part marking information	www.vishay.com/doc?95008					
Packaging information	www.vishay.com/doc?95032					



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D²PAK, TO-262

DIMENSIONS - D²PAK in millimeters and inches



SYMBOL	MILLIN	MILLIMETERS		HES	NOTES
	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.06	4.83	0.160	0.190	
A1	0.00	0.254	0.000	0.010	
b	0.51	0.99	0.020	0.039	
b1	0.51	0.89	0.020	0.035	4
b2	1.14	1.78	0.045	0.070	
b3	1.14	1.73	0.045	0.068	4
С	0.38	0.74	0.015	0.029	
c1	0.38	0.58	0.015	0.023	4
c2	1.14	1.65	0.045	0.065	
D	8.51	9.65	0.335	0.380	2

SYMBOL	MILLIN	IETERS	INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.	NOTES
D1	6.86	8.00	0.270	0.315	3
E	9.65	10.67	0.380	0.420	2, 3
E1	7.90	8.80	0.311	0.346	3
е	2.54 BSC		0.100 BSC		
Н	14.61	15.88	0.575	0.625	
L	1.78	2.79	0.070	0.110	
L1	-	1.65	-	0.066	3
L2	1.27	1.78	0.050	0.070	
L3	0.25 BSC		0.010	BSC	
L4	4.78	5.28	0.188	0.208	

Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- $^{(3)}\,$ Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inch

(7) Outline conforms to JEDEC outline TO-263AB

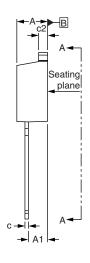
Document Number: 95014 Revision: 31-Mar-09

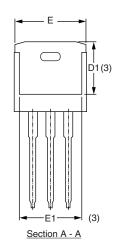
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D²PAK, TO-262



DIMENSIONS - TO-262 in millimeters and inches





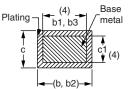
⊕ 0.010**⋒**|A**⋒**|B

Lead assignments



<u>Diodes</u>
1. - Anode (two die)/open (one die)
2., 4. - Cathode

3. - Anode



Section B - B and C - C Scale: None

CYMPOL	MILLIMETERS		INC	INCHES		
SYMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	
Α	4.06	4.83	0.160	0.190		
A1	2.03	3.02	0.080	0.119		
b	0.51	0.99	0.020	0.039		
b1	0.51	0.89	0.020	0.035	4	
b2	1.14	1.78	0.045	0.070		
b3	1.14	1.73	0.045	0.068	4	
С	0.38	0.74	0.015	0.029		
c1	0.38	0.58	0.015	0.023	4	
c2	1.14	1.65	0.045	0.065		
D	8.51	9.65	0.335	0.380	2	
D1	6.86	8.00	0.270	0.315	3	
Е	9.65	10.67	0.380	0.420	2, 3	
E1	7.90	8.80	0.311	0.346	3	
е	2.54 BSC		0.100) BSC		
L	13.46	14.10	0.530	0.555		
L1	-	1.65	-	0.065	3	
L2	3.56	3.71	0.140	0.146		

Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Controlling dimension: inches

(6) Outline conform to JEDEC TO-262 except A1 (maximum), b (minimum) and D1 (minimum) where dimensions derived the actual package outline

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